



January 2015

FDMC7696

N-Channel PowerTrench[®] MOSFET

30 V, 12 A, 11.5 mΩ

Features

- Max $r_{DS(on)}$ = 11.5 mΩ at $V_{GS} = 10$ V, $I_D = 12$ A
- Max $r_{DS(on)}$ = 14.5 mΩ at $V_{GS} = 4.5$ V, $I_D = 10$ A
- High performance technology for extremely low $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

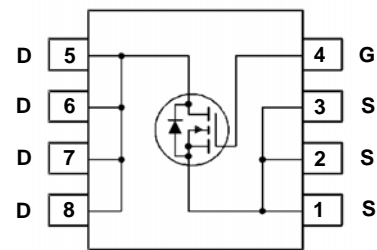
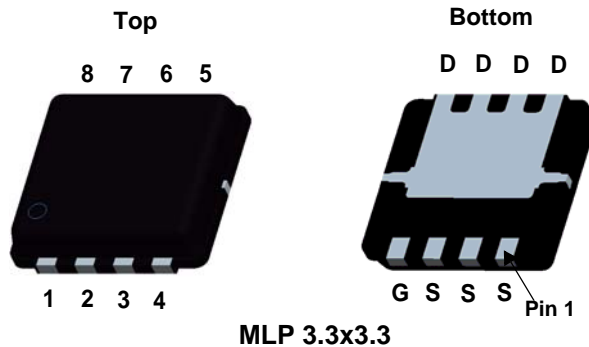


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench[®] process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Applications

- DC/DC Buck Converters
- Notebook battery power management
- Load Switch in Notebook



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{DSI}	Drain to Source Transient Voltage ($t_{\text{Transient}} < 100$ ns)	33	V
V_{GS}	Gate to Source Voltage (Note 4)	± 20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	20	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	38	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	12	
	-Pulsed	50	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	21	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	25	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.4	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7696	FDMC7696	MLP 3.3x3.3	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		14		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = 20\ \text{V}$, $V_{DS} = 0\ \text{V}$			100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	1.2	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C		-6		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$, $I_D = 12\ \text{A}$		8.5	11.5	m Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 10\ \text{A}$		11.5	14.5	
		$V_{GS} = 10\ \text{V}$, $I_D = 12\ \text{A}$, $T_J = 125^\circ\text{C}$		11.6	15.7	
g_{FS}	Forward Transconductance	$V_{DS} = 5\ \text{V}$, $I_D = 12\ \text{A}$		45		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$		1075	1430	pF
C_{oss}	Output Capacitance			380	505	pF
C_{rss}	Reverse Transfer Capacitance			40	55	pF
R_g	Gate Resistance		0.2	1.0	2.0	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\ \text{V}$, $I_D = 12\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_{GEN} = 6\ \Omega$		9	18	ns
t_r	Rise Time			2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	33	ns
t_f	Fall Time			2	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $10\ \text{V}$	$V_{DD} = 15\ \text{V}$, $I_D = 12\ \text{A}$	16	22	nC
Q_g	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $5\ \text{V}$		8	11	nC
Q_{gs}	Gate to Source Charge			3.2		nC
Q_{gd}	Gate to Drain "Miller" Charge			1.8		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$, $I_S = 1.9\ \text{A}$ (Note 2)		0.75	1.2	V
		$V_{GS} = 0\ \text{V}$, $I_S = 12\ \text{A}$ (Note 2)		0.84	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 12\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		25	40	ns
Q_{rr}	Reverse Recovery Charge			9	18	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $53^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. E_{AS} of 21 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 0.3\ \text{mH}$, $I_{AS} = 12\ \text{A}$, $V_{DD} = 27\ \text{V}$, $V_{GS} = 10\ \text{V}$.

4. As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

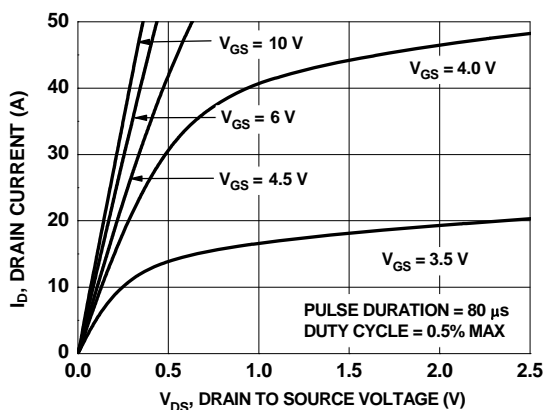


Figure 1. On Region Characteristics

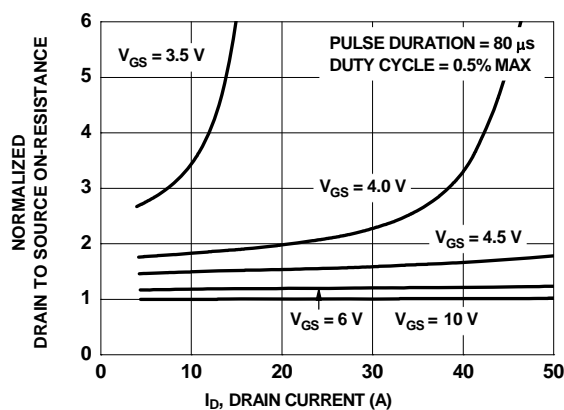


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

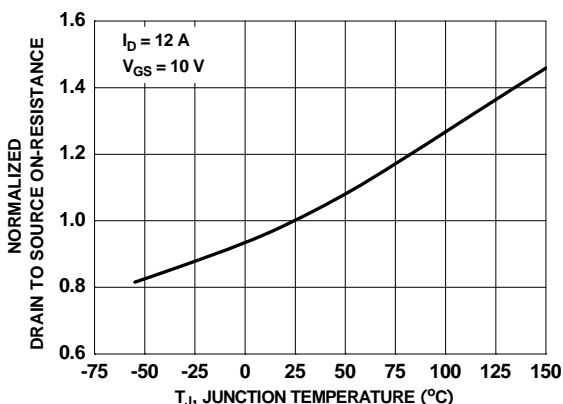


Figure 3. Normalized On Resistance vs Junction Temperature

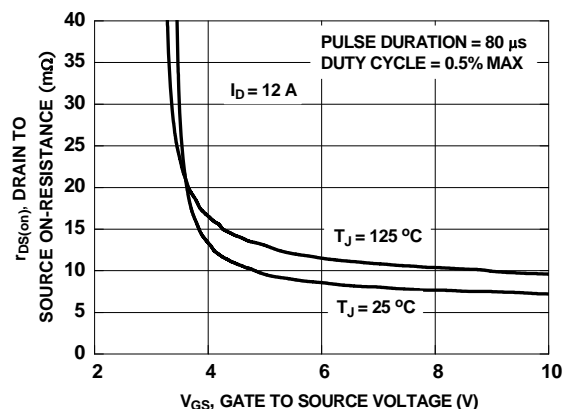


Figure 4. On-Resistance vs Gate to Source Voltage

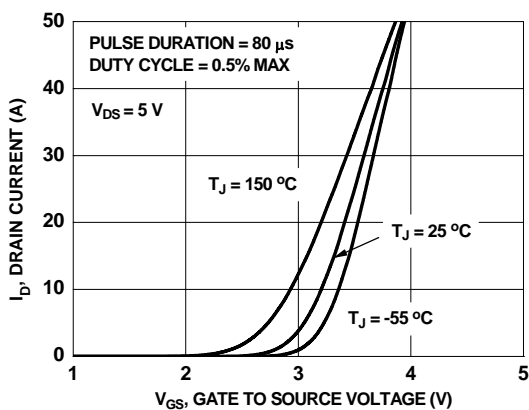


Figure 5. Transfer Characteristics

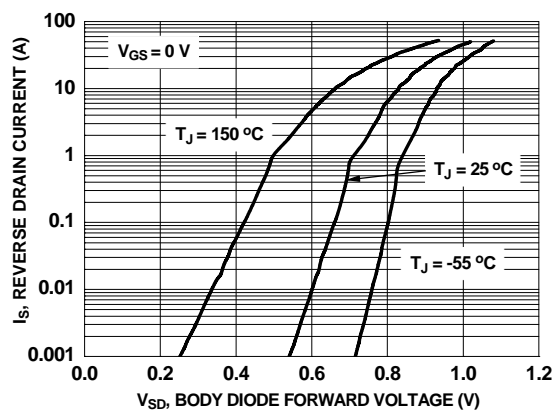


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

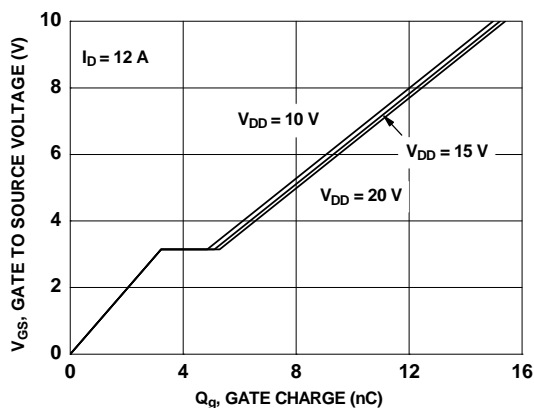


Figure 7. Gate Charge Characteristics

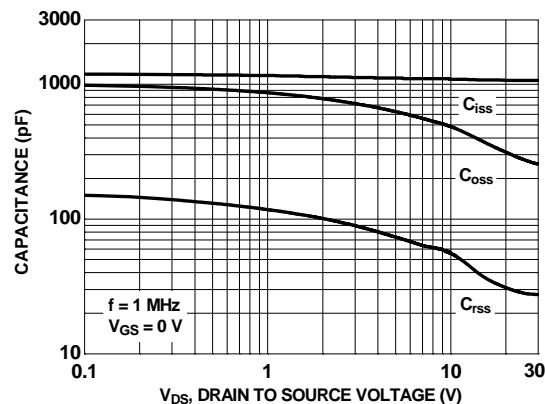


Figure 8. Capacitance vs Drain to Source Voltage

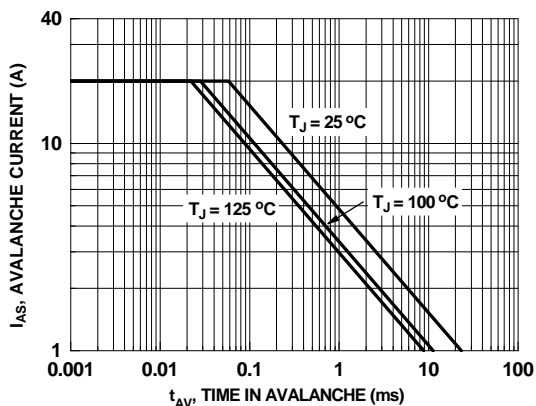


Figure 9. Unclamped Inductive Switching Capability

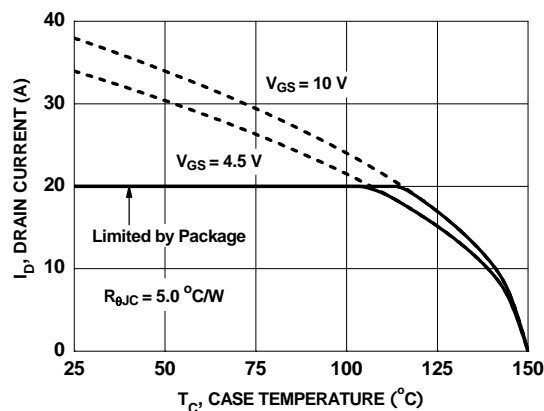


Figure 10. Maximum Continuous Drain Current vs Case Temperature

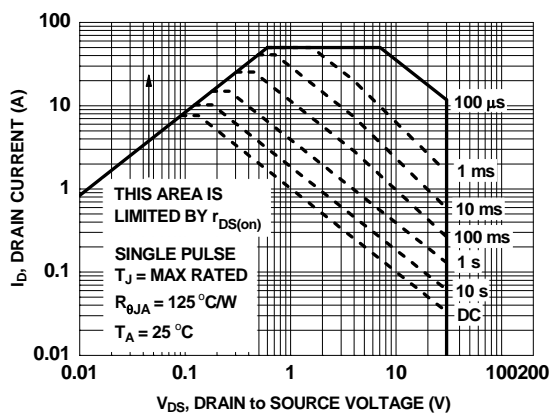


Figure 11. Forward Bias Safe Operating Area

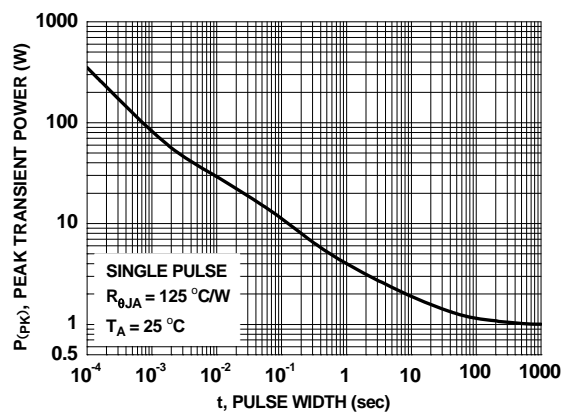


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

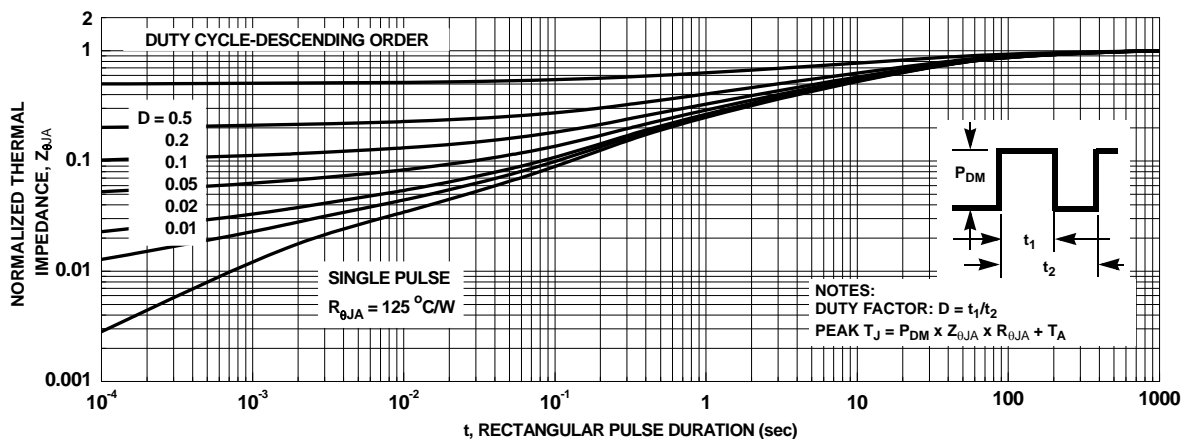
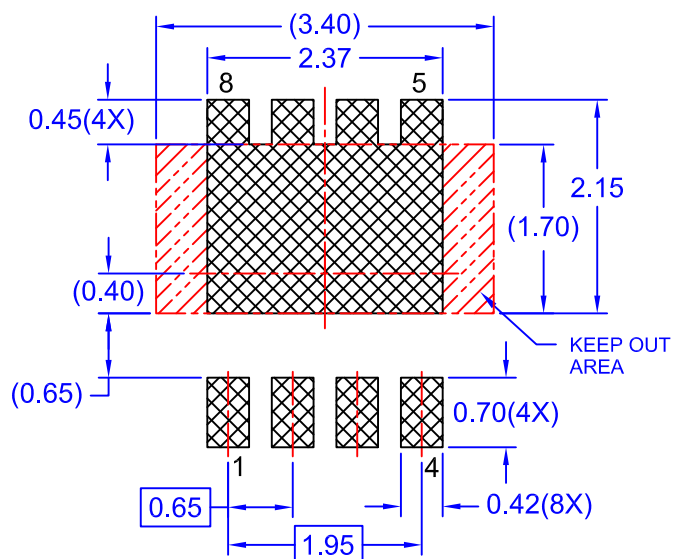
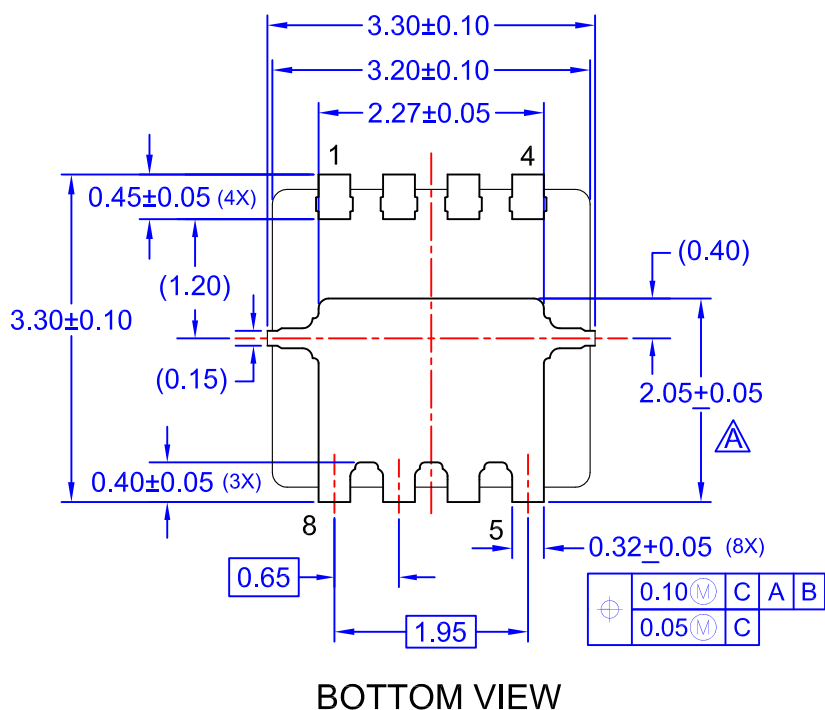
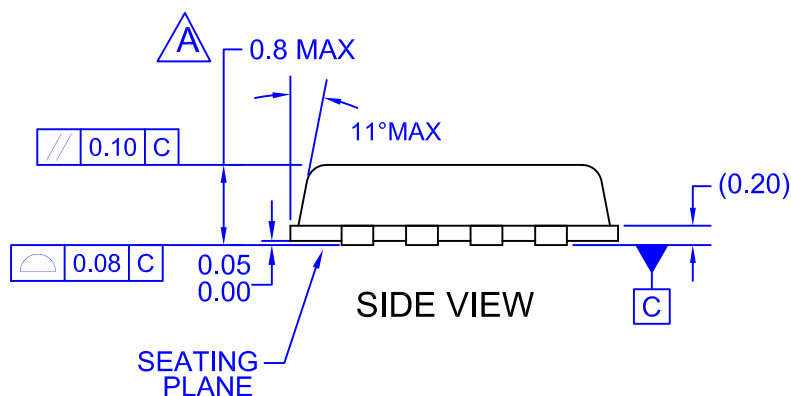
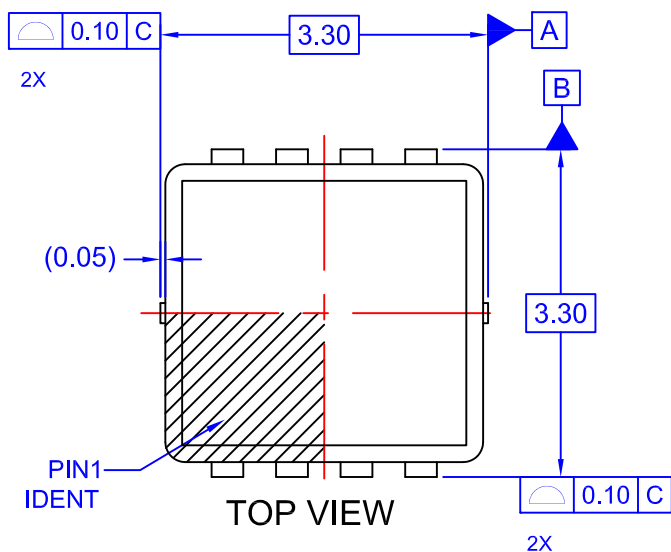


Figure 13. Junction-to-Ambient Transient Thermal Response Curve



NOTES:

- A. EXCEPT AS NOTED, PACKAGE CONFORMS TO JEDEC REGISTRATION MO-240 VARIATION BA.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY.
- E. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS.
- F. FLANGE DIMENSIONS INCLUDE INTERTERMINAL FLASH OR PROTRUSION. INTERTERMINAL FLASH OR PROTRUSION SHALL NOT EXCEED 0.25MM PER SIDE.
- G. IT IS RECOMMENDED TO HAVE NO TRACES OR VIA WITHIN THE KEEP OUT AREA.
- H. DRAWING FILENAME: MKT-MLP08Trev4.
- I. GENERAL RADII FOR ALL CORNERS SHALL BE 0.20MM MAX.



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